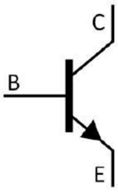
TO-252 NPN Silicon NPN transistor in a TO-252 Plastic Package.

AEC-Q101

High collector-Emitter breakdown voltage, Suitable for transformer, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

High voltage general purpose applications, Meet the stringent requirements of automotive applications.



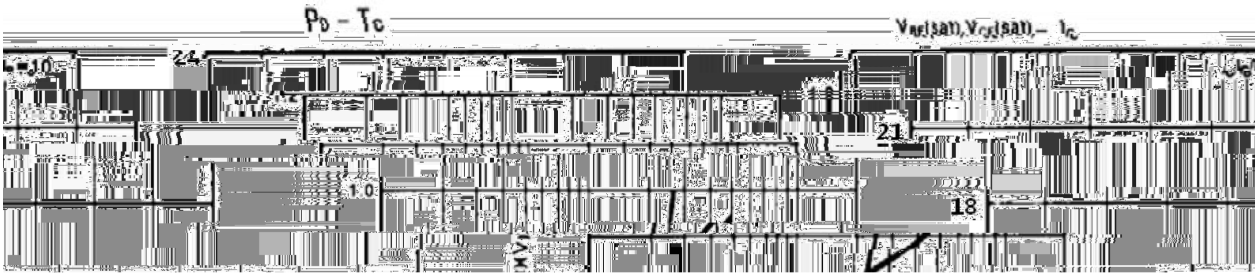
[redacted]

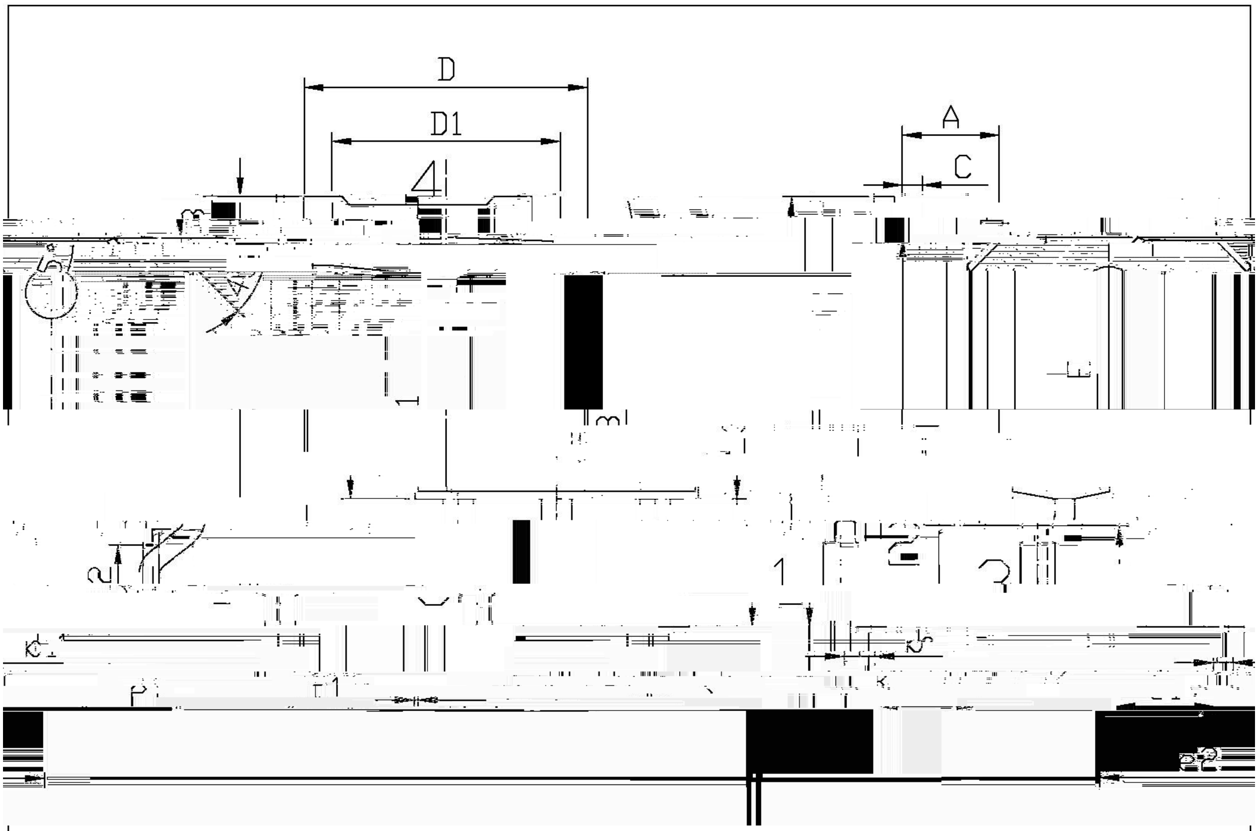
PIN1 Base PIN 2,4 Collector PIN 3 Emitter

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C	1.56	W
Collector Power Dissipation	$P_C(T_C=25\ \ )$	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ

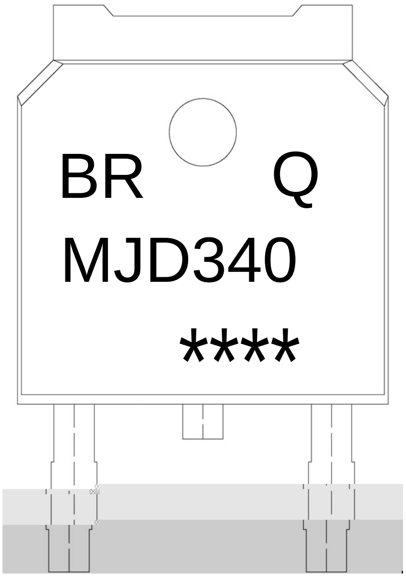

PD – TC
VBE(sat),VCE(sat) – IC
1.0
21
18



单位：mm

Symbol	Dimensions In Millimeters Min.	Max.	Symbol	Dimensions In Millimeters Min.	Max.
E	5.95	6.25	A	2.20	2.40
[illegible]	2.24	2.34	B	0.95	1.25
e1	4.43	4.73	b	0.70	0.90
L1	9.85	10.35	b1	0.45	0.55
C	0.45	0.55	L2	1.70	2.00
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252



BR

Q

MJD340

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Note:

BR:	Company Code
Q:	Automobile halogen-free product Code
MJD340:	Product Type
****:	Lot No. Code, code change with Lot No